Everspin Spin Torque MRAM showcased as the first storage class memory at the OpenPOWER™ Summit.

Chandler, AZ, April 7, 2016 Everspin Technologies today announced that IBM has demonstrated Everspin's latest Spin Torque DDR3 MRAM in the ConTutto platform in a Power8 system. The demonstration showed show how Everspin's DDR3 ST-MRAM operates as persistent memory, accelerating storage and server applications. ConTutto is an IBM research configurable platform for innovation in the memory subsystem of an OpenPOWER node. The DDR3 interface on the Everspin Spin Torque MRAM makes it easy for developers to take advantage of the write speed and persistence of MRAM. In his keynote address, Brad McCredie, Vice President and IBM Fellow, described this as the first functional demonstration of a storage class memory in an enterprise system.

"We are very excited that IBM has demonstrated the value of our ST-MRAM as a persistent memory in an actual enterprise environment," said Scott Sewell, Vice President of Worldwide Sales and Marketing for Everspin Technologies. "This is further validation of the progress we have made in bringing a new class of memory to developers of enterprise storage and server systems."

Everspin recently joined the OpenPOWER Foundation as a silver member. Please visit the OpenPOWER Summit Pavilion from April 5-8, 2016 at the San Jose Convention Center to see the IBM demonstration. To learn more about OpenPOWER Summit 2016 and the Pavilion hours please visit
http://openpowerfoundation.org/openpower-summit-2016/.

About Everspin Technologies

Everspin Technologies is the worldwide leader in designing, manufacturing, and commercially shipping discrete and embedded Magnetoresistive RAM (MRAM) and Spin-Torque MRAM (ST-MRAM) into markets and applications where data persistence and integrity, low latency, and security are paramount. With over 60 Million MRAM and ST-MRAM products deployed in data center, cloud storage, energy, industrial, automotive, and transportation markets, Everspin has built the strongest and fastest growing foundation of MRAM users in the world. With an intellectual property portfolio of more than 500 active patents and applications, Everspin leads the market in development of both in-plane and perpendicular magnetic tunnel junction (MTJ) ST-MRAM bit cells. Everspin has established high-quality manufacturing worldwide, along with enabling a full turn-key 300mm high-volume foundry partner for advanced technology nodes including 40nm, 28nm and beyond. In addition to launching discrete memory solutions with new densities and advanced interfaces, including the world's first commercialization and volume shipments of ST-MRAM, Everspin is delivering on the company's strategy to proliferate MRAM and ST-MRAM as mainstream embedded memories for use in MCUs, GPUs, DSPs, Application Processors, and ASICs, earning Everspin its description as "The MRAM Company". www.everspin.com